

PSMN2R8-40PS

N-channel TO220 40 V 2.8 mΩ standard level MOSFET 11 February 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static charac	teristics		'	_			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 100 °C; Fig. 12; Fig. 13		-	-	4.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 13	[2]	-	2.3	2.8	mΩ
Dynamic cha	racteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 20 V;		-	17	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15		-	71	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 40 V; unclamped; R_{GS} = 50 Ω		-	-	407	mJ

- [1] Continuous current rating is limited by package.[2] Measured 3 mm from package.

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	704	
3	S	source		G—U: 4
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

Ordering information

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
PSMN2R8-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

Marking

Table 4. **Marking codes**

Type number	Marking code
PSMN2R8-40PS	PSMN2R8-40PS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	[1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	797	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	211	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
Is	source current	T _{mb} = 25 °C		-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	797	Α
Avalanche i	ruggedness	'		1		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 40 V; unclamped; R_{GS} = 50 Ω		-	407	mJ

[1] Continuous current rating is limited by package.

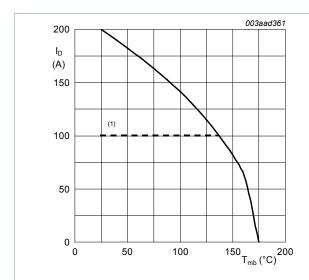


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{\it GS} \geq 10\,V \label{eq:VGS}$$
 (1) Capped at 100 A due to package.

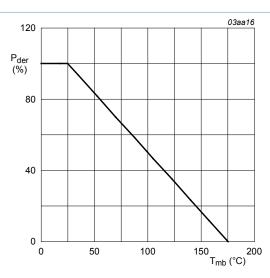


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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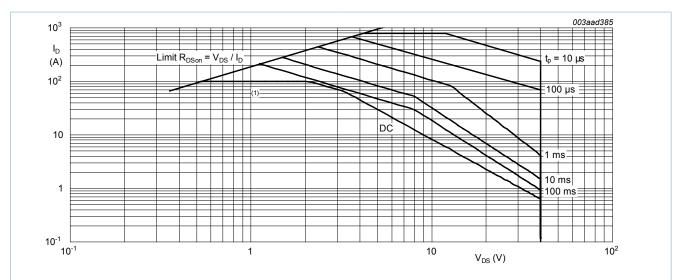


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 T_{nb} = 25 °C; I_{DM} is a single pulse; (1) Capped at 100 A due to package

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.4	0.7	K/W

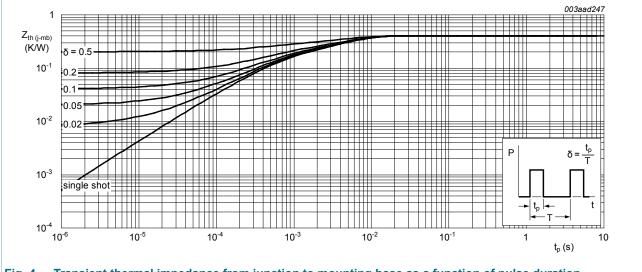


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

V V V 4.6 V
. V 4.6 V
4.6 V
V
4 V
10 μΑ
150 μΑ
100 nA
100 nA
4.5 mΩ
5.6 mΩ
2.8 mΩ
- Ω
nC
nC
· nC
· nC
· nC
nC
· V
pF
1 1 1

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{rss}	reverse transfer capacitance			-	464	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_L = 0.8 Ω ; V_{GS} = 10 V;		-	28	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$		-	29	-	ns
t _{d(off)}	turn-off delay time			-	52	-	ns
t _f	fall time			-	23	-	ns
Source-dra	in diode				'	'	
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	0.85	1.2	V
t _{rr}	reverse recovery time	I_S = 40 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V		-	47	-	ns
Q _r	recovered charge	I_S = 40 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C		-	61	-	nC

[1] Measured 3 mm from package.

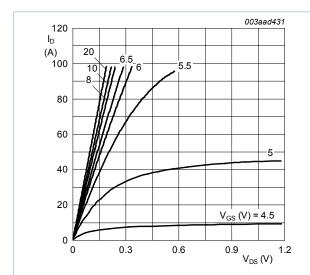


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



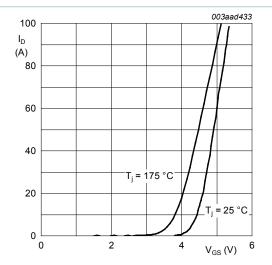


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

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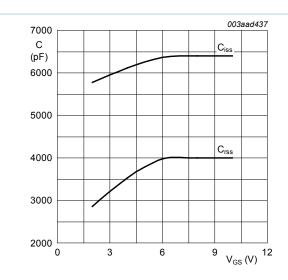


Fig. 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHz$$

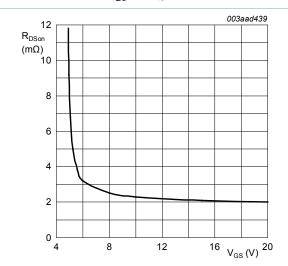


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25\,^{\circ}C; I_D = 25A$$

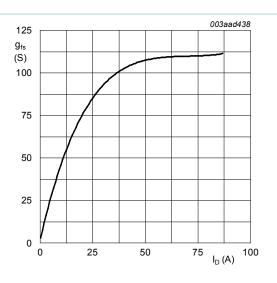


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$$

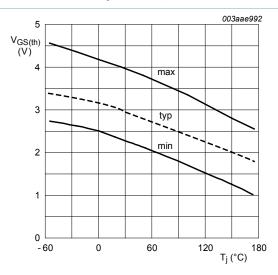


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

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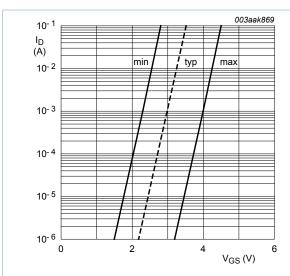


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

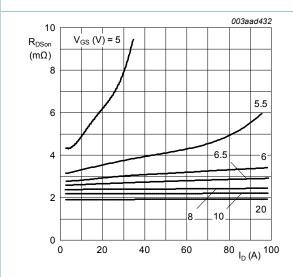


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

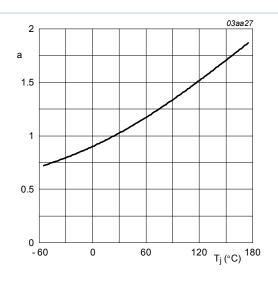


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

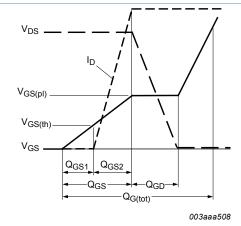


Fig. 14. Gate charge waveform definitions

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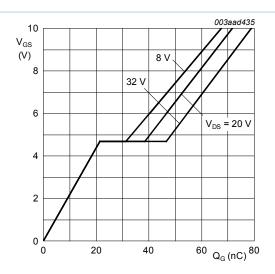


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 10A$$

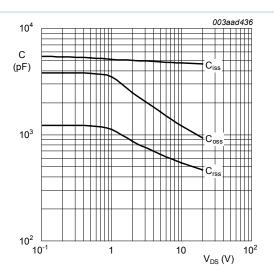


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

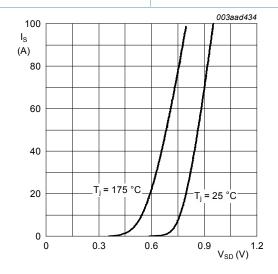
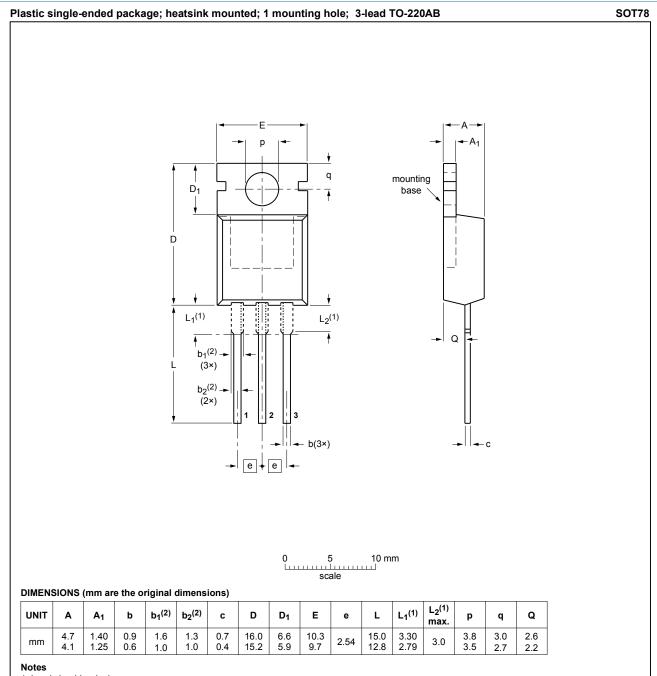


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

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11. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

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Document status [1][2]	Product status [3]	Definition
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